

# MC74HC03A

## Quad 2-Input NAND Gate with Open-Drain Outputs High-Performance Silicon-Gate CMOS

The MC74HC03A is identical in pinout to the LS03. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

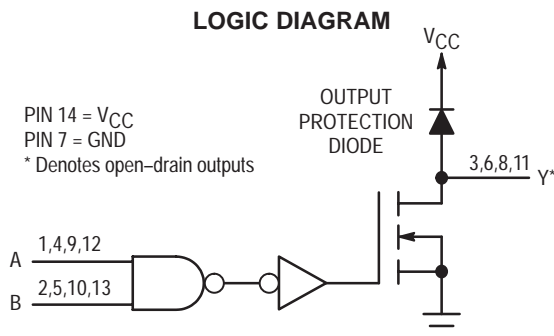
The HC03A NAND gate has, as its outputs, a high-performance MOS N-Channel transistor. This NAND gate can, therefore, with a suitable pullup resistor, be used in wired-AND applications. Having the output characteristic curves given in this data sheet, this device can be used as an LED driver or in any other application that only requires a sinking current.

- Output Drive Capability: 10 LSTTL Loads With Suitable Pullup Resistor
- Outputs Directly Interface to CMOS, NMOS and TTL
- High Noise Immunity Characteristic of CMOS Devices
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1µA
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 28 FETs or 7 Equivalent Gates

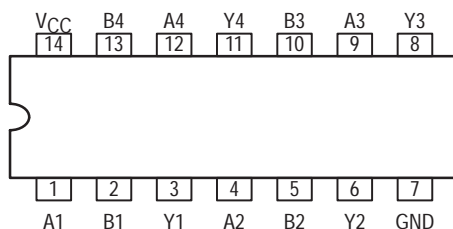
### DESIGN GUIDE

Criteria	Value	Unit
Internal Gate Count*	7.0	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	µW
Speed Power Product	0.0075	pJ

\* Equivalent to a two-input NAND gate

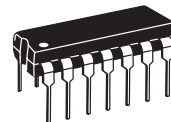


### Pinout: 14-Lead Packages (Top View)

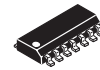


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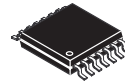
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PDIP-14  
N SUFFIX  
CASE 646

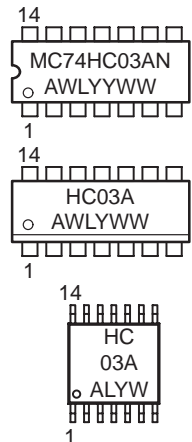


SOIC-14  
D SUFFIX  
CASE 751A



TSSOP-14  
DT SUFFIX  
CASE 948G

### MARKING DIAGRAMS



A = Assembly Location  
WL or L = Wafer Lot  
YY or Y = Year  
WW or W = Work Week

### FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z = High Impedance

### ORDERING INFORMATION

Device	Package	Shipping
MC74HC03AN	PDIP-14	2000 / Box
MC74HC03AD	SOIC-14	55 / Rail
MC74HC03ADR2	SOIC-14	2500 / Reel
MC74HC03ADT	TSSOP-14	96 / Rail
MC74HC03ADTR2	TSSOP-14	2500 / Reel

# MC74HC03A

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V	
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V	
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V	
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA	
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA	
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA	
P <sub>D</sub>	Power Dissipation in Still Air	Plastic DIP†	750	mW
		SOIC Package†	500	
		TSSOP Package†	450	
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C	
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds	Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	V <sub>CC</sub> = 2.0 V	0	1000	ns
		V <sub>CC</sub> = 4.5 V	0	500	
		V <sub>CC</sub> = 6.0 V	0	400	

## DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub> V	Guaranteed Limit			Unit
				-55 to 25°C	≤85°C	≤125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1V or V <sub>CC</sub> - 0.1V  I <sub>out</sub>   ≤ 20μA	2.0	1.50	1.50	1.50	V
			3.0	2.10	2.10	2.10	
			4.5	3.15	3.15	3.15	
			6.0	4.20	4.20	4.20	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1V or V <sub>CC</sub> - 0.1V  I <sub>out</sub>   ≤ 20μA	2.0	0.50	0.50	0.50	V
			3.0	0.90	0.90	0.90	
			4.5	1.35	1.35	1.35	
			6.0	1.80	1.80	1.80	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>out</sub> = 0.1V or V <sub>CC</sub> - 0.1V  I <sub>out</sub>   ≤ 20μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 2.4mA  I <sub>out</sub>   ≤ 4.0mA  I <sub>out</sub>   ≤ 5.2mA	3.0	0.26	0.33	0.40	
			4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0μA	6.0	1.0	10	40	μA
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	6.0	±0.5	±5.0	±10	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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## AC CHARACTERISTICS ( $C_L = 50\text{pF}$ , Input $t_r = t_f = 6\text{ns}$ )

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			-55 to 25°C	≤85°C	≤125°C	
t <sub>PLZ</sub> , t <sub>PZL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0	120	150	180	ns
		3.0	45	60	75	
		4.5	24	30	36	
		6.0	20	26	31	
t <sub>T LH</sub> , t <sub>T HL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0	75	95	110	ns
		3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C <sub>in</sub>	Maximum Input Capacitance		10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C <sub>PD</sub>	Power Dissipation Capacitance (Per Buffer)*	Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V		pF
		8.0		

\* Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# MC74HC03A

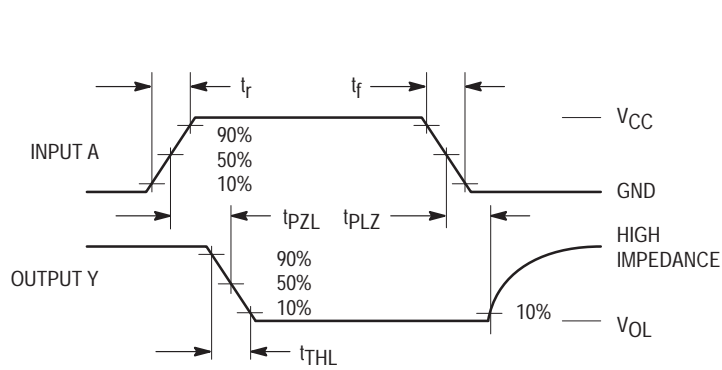
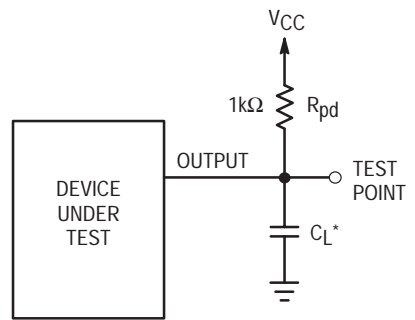
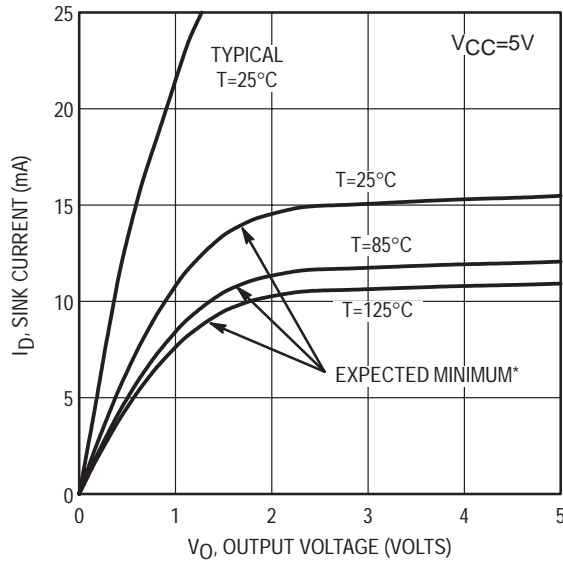


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit



\*The expected minimum curves are not guarantees, but are design aids.

Figure 3. Open-Drain Output Characteristics

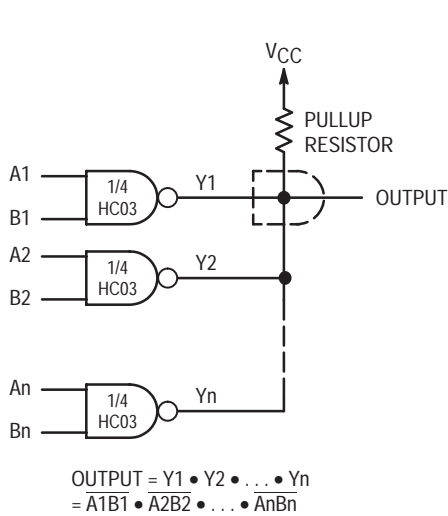


Figure 4. Wired AND

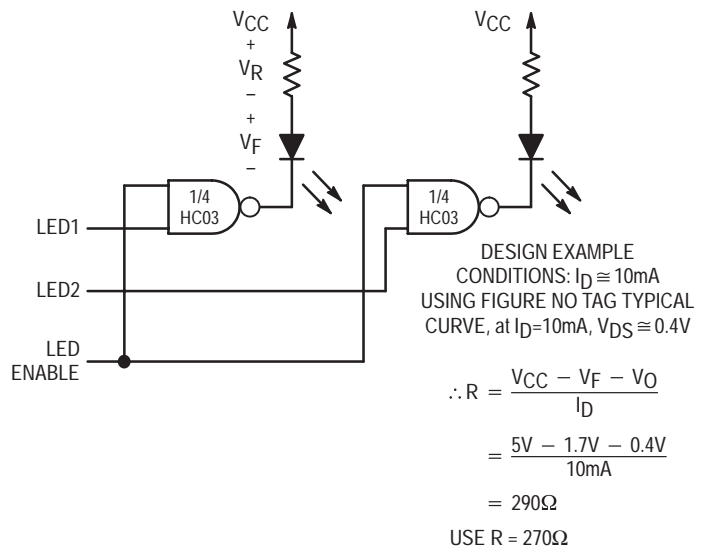


Figure 5. LED Driver With Blanking

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## PACKAGE DIMENSIONS

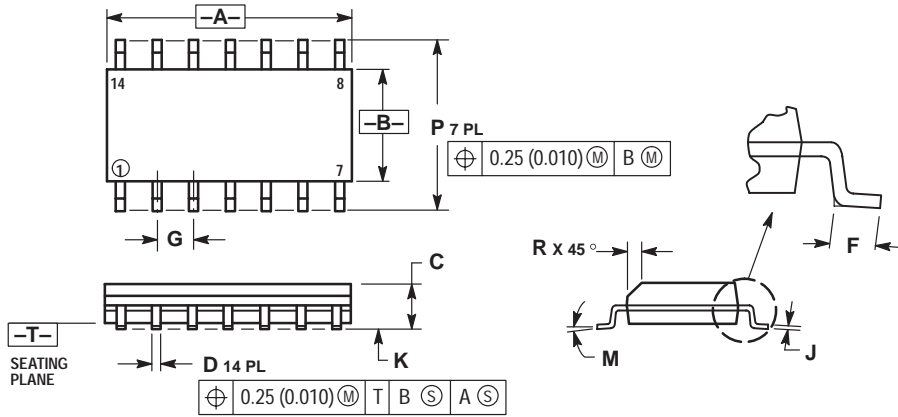
**PDIP-14  
N SUFFIX  
CASE 646-06  
ISSUE L**



- NOTES:
- LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
  - DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  - DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  - ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62 BSC	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

**SOIC-14  
D SUFFIX  
CASE 751A-03  
ISSUE F**



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: MILLIMETER.
  - DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  - MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  - DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

# MC74HC03A

## PACKAGE DIMENSIONS

TSSOP-14  
DT SUFFIX  
CASE 948G-01  
ISSUE O



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -V-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**Notes**

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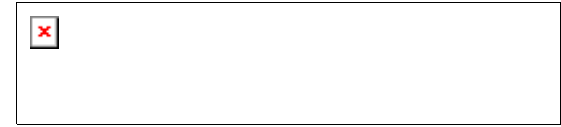
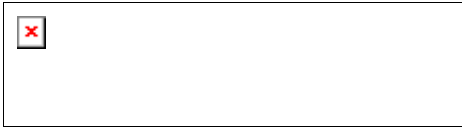
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Item	Short Desc	Size
<a href="#">Data Sheet</a>	Quad 2-Input NAND Gate With Open-Drain Outputs	151 kB PDF

**Device MC74HC03A**  
**Quad 2-Input NAND Gate with Drain**

High-Performance Silicon-Gate CMOS

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- Outputs Directly Interface to CMOS, NMOS and TTL
- High Noise Immunity Characteristic of CMOS Devices
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1µA
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 28 FETs or 7 Equivalent Gates

**Orderable Parts**

Action	Orderable Part	Short Desc.	Package Desc.	Pin Count	Case Outline	Status	Price/Unit	Pack Qty
--------	----------------	-------------	---------------	-----------	--------------	--------	------------	----------



N/A	MC74HC03AD	Quad 2- Input NOR Gate with Drain	SOIC	14	<a href="#">751A-03</a>	Active	\$0.160	55
N/A	MC74HC03ADR2	Tape and Reel	SOIC	14	<a href="#">751A-03</a>	Active	\$0.160	2500
N/A	MC74HC03ADTEL	Tape and Reel	TSSOP	14	<a href="#">948G-01</a>	Active	\$0.200	2000
N/A	MC74HC03ADTR2	Tape and Reel	TSSOP	14	<a href="#">948G-01</a>	Active	\$0.200	2500
N/A	MC74HC03AFEL	Tape and Reel	SOIC EIAJ	14	<a href="#">940A-03</a>	Active	\$0.160	2000
N/A	MC74HC03ADT	Quad 2- Input NAND Gate with Drain	TSSOP	14	<a href="#">948G-01</a>	Active	\$0.200	96
N/A	MC74HC03AF	Quad 2- Input NAND Gate with Drain	SOIC EIAJ	14	<a href="#">940A-03</a>	Active	\$0.160	50
N/A	MC74HC03AFL1	Tape and Reel	SOIC EIAJ	14	<a href="#">940A-03</a>	LifeTime		
N/A	MC74HC03AFL2	Tape and Reel	SOIC EIAJ	14	<a href="#">940A-03</a>	LifeTime		
N/A	MC74HC03AFR1	Tape and Reel	SOIC EIAJ	14	<a href="#">940A-03</a>	Obsolete		

N/A	MC74HC03AFR2	Tape and Reel	SOIC EIAJ	14	<a href="#">940A-03</a>	LifeTime		
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